



LOW NOISE, HIGH GAIN, GaAs FET PHOTODETECTOR-AMPLIFIER MODULE

- ULTRA LOW NOISE - Down to 15fW/√Hz
- HIGH BANDWIDTH – Up to 60MHz
- AC or DC Coupled Output
- HIGH GAIN – 1MV/A Transimpedance
- SILICON OR InGaAs PIN's & APD's
- DIRECTIVE 2011/65/EU (RoHS II) Compliant



DESCRIPTION:

The **712B Series** Low Noise, High Bandwidth Photodetector-Amplifier Modules offer high gain amplifiers with the flexibility of incorporating various silicon and InGaAs photodetectors for low signal level sensing applications. The **712B Series** is based on the **312B Series** transimpedance amplifiers. Consult factory for different detectors.

SPECIFICATIONS:

Input	Silicon or InGaAs photodetector (See table for characteristics.) 3μA maximum DC light-induced current	Power	+12 to +15VDC at 60mA typical
Output		Temperature	-20° to +70°C
Load	50Ω	Connections	
Swing	> +3V pk	Input	Photodetector
Coupling	AC (add -AC to part number) DC (add -DC to part number) AC cut-out frequency of ≤ 250Hz	Output	SMB (SMB to BNC cable provided)
Gain	1MV/A transimpedance Multiply transimpedance gain by detector responsivity at peak wavelength to get V/W in table.	Power	Solder Pins
Polarity	Non-Inverting Positive output when flux applied	Bias	9V internal bias may be over-ridden by external supply. External Bias Pin decoupled with 0.01μF, 1kV capacitor
		Size	1.98" x 3.2" x 0.5"
		Weight	4 ounces
		MTBF	> 1x10 ⁷ hrs

Specifications subject to change without notice.



APPLICATIONS:

High Speed, Low Light Level Sensing, LIDAR

